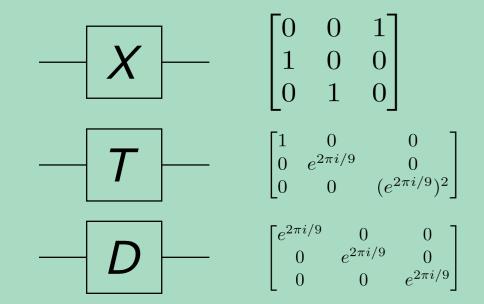
RANDOMISED BENCHMARKING OF UNIVERSAL QUTRIT GATES

Explicit Randomised Benchmarking qutrit schemes are limited to Clifford gates. We introduce a scheme to characterise a qutrit T gate.



Our scheme is a **feasible** extension to qutrits of the Dihedral Benchmarking scheme [Carignan-Dugas *et. al.*]. Our scheme is the synthesis of the **Fourier method** [Merkel *et. al.*] applied to non-Clifford gates.

Our scheme is important for experimental groups with qutrit implementations [Morvan *et. al.*], theorists working on Randomised Benchmarking methods, and in general theorists interested in the application of Representation Theory in Quantum Information.

<u>David Amaro-Alcalá</u>^{1,2}, Barry C. Sanders¹, Hubert de Guise^{1,2}.

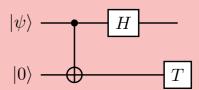


BACKGROUND

Randomized Benchmarking (RB) estimates quantum gate quality by comparing the behaviour of ideal and noisy gates, via the average gate fidelity F [Magesan et. al.].



RB is used to characterize Clifford gates, T gates require an extension of the RB scheme for their characterization.



A **qutrit** is a three-level quantum system that offers advantages over qubits and is widely available in different quantum information implementations [Wang *et. al.*].

RESULTS

RB assumes gates approximately implement transformations of a group; we introduce the HyperDihedral group to characterise a T gate. The HyperDihedral group is generated by X,T, and D.

The name HyperDihedral is given because it is a generalisation of the Dihedral group.

$$\begin{array}{c|cccc} \textbf{Dihedral} & \textbf{HyperDihedral} \\ \hline C_2 \ltimes C_8 & C_3 \ltimes C_9 \times C_9 \\ \end{array}$$

We obtained the expression for the average gate fidelity for the HyperDihedral group; it has **two parameters**, accessible by using two different **initial states**. Our expression

$$F = \frac{3}{4}(1 + 2r_0 + 6r_+) + \frac{1}{4}$$
.

is valid for state imperfections and gatedependent errors.

Our method is feasible because it requires the same resources in already established RB schemes [Wang et. al.].

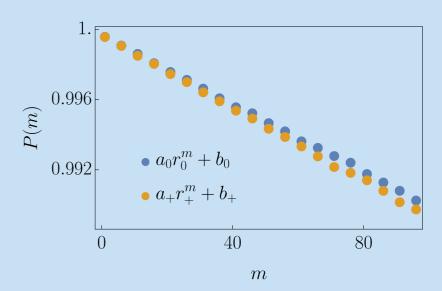


Figure 1: Survival probability P vs circuit depth m curve illustrating the relationship between the parameters that can be extracted from it to estimate the average gate fidelity shown in the second column. Density matrices $|0\rangle\langle 0|$ and $|+\rangle\langle +|$, denote the initial state required to obtain parameters r_0 and r_+ , respectively.

Alberta

